

IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



BT138B-600G

4Q Triac

26 September 2013

Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT404 (D2PAK) surface-mountable plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

2. Features and benefits

- High blocking voltage capability
- Least sensitive gate for highest noise immunity
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants

3. Applications

- General purpose motor control
- General purpose switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	-	600	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$; $t_p = 20 \text{ ms}$; Fig. 4 ; Fig. 5		-	-	95	A
T_j	junction temperature			-	-	125	$^\circ\text{C}$
$I_{T(\text{RMS})}$	RMS on-state current	full sine wave; $T_{mb} \leq 99^\circ\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3		-	-	12	A
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12 \text{ V}$; $I_T = 0.1 \text{ A}$; T2+ G+; $T_j = 25^\circ\text{C}$; Fig. 7		-	5	50	mA
		$V_D = 12 \text{ V}$; $I_T = 0.1 \text{ A}$; T2+ G-; $T_j = 25^\circ\text{C}$; Fig. 7		-	8	50	mA



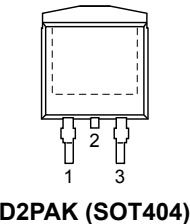
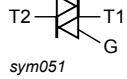
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Symbol	Parameter	Conditions		Min	Typ	Max	Unit
		$V_D = 12 \text{ V}$; $I_T = 0.1 \text{ A}$; T2- G-; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 7		-	10	50	mA
		$V_D = 12 \text{ V}$; $I_T = 0.1 \text{ A}$; T2- G+; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 7		-	22	100	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402 \text{ V}$; $T_j = 125 \text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		200	250	-	V/ μ s

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2	 D2PAK (SOT404)	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT138B-600G	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 99$ °C; Fig. 1 ; Fig. 2 ; Fig. 3		-	12	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig. 4 ; Fig. 5		-	95	A
		full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms		-	105	A
I^2t	I^2t for fusing	$t_p = 10$ ms; sine-wave pulse		-	45	A^2s
dI_T/dt	rate of rise of on-state current	$I_T = 20$ A; $I_G = 0.2$ A; $dI_G/dt = 0.2$ A/ μ s; T2+ G+		-	50	A/μ s
		$I_T = 20$ A; $I_G = 0.2$ A; $dI_G/dt = 0.2$ A/ μ s; T2+ G-		-	50	A/μ s
		$I_T = 20$ A; $I_G = 0.2$ A; $dI_G/dt = 0.2$ A/ μ s; T2- G-		-	50	A/μ s
		$I_T = 20$ A; $I_G = 0.2$ A; $dI_G/dt = 0.2$ A/ μ s; T2- G+		-	10	A/μ s
I_{GM}	peak gate current			-	2	A
P_{GM}	peak gate power			-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.5	W
T_{stg}	storage temperature			-40	150	°C
T_j	junction temperature			-	125	°C

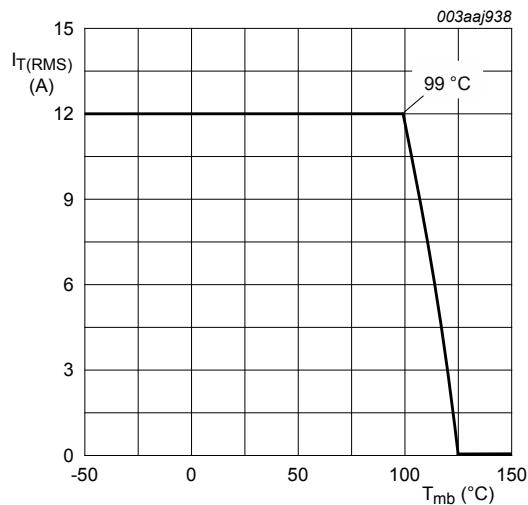
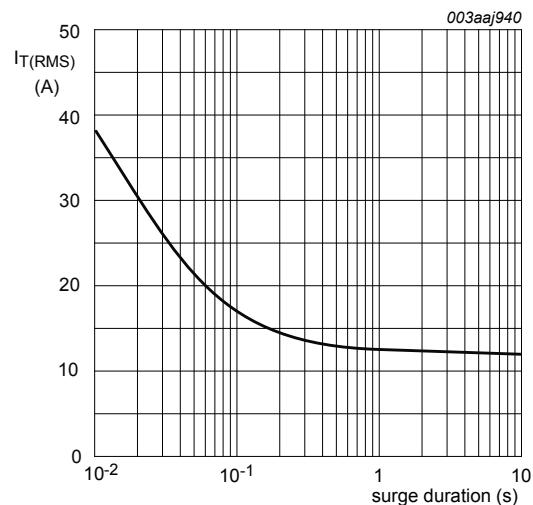
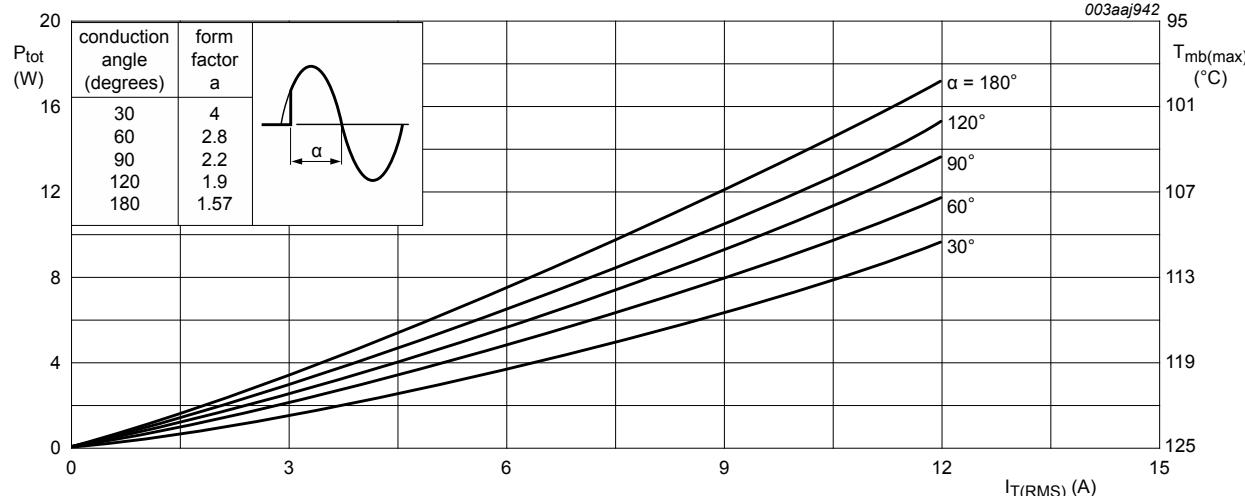


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz; Tmb = 99 °C

Fig. 2. RMS on-state current as a function of surge duration; maximum values



α = conduction angle

a = form factor = $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

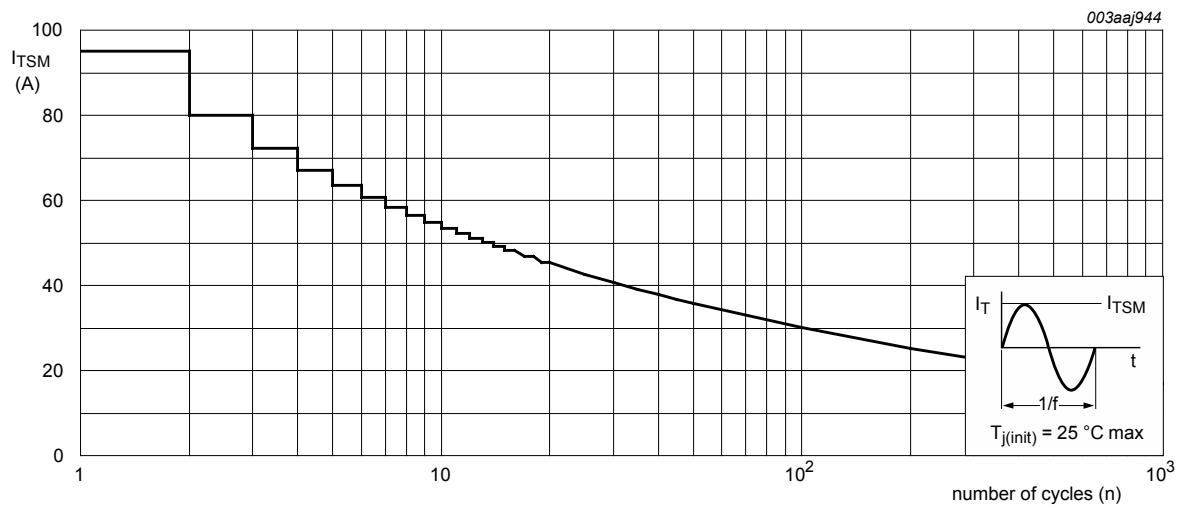


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

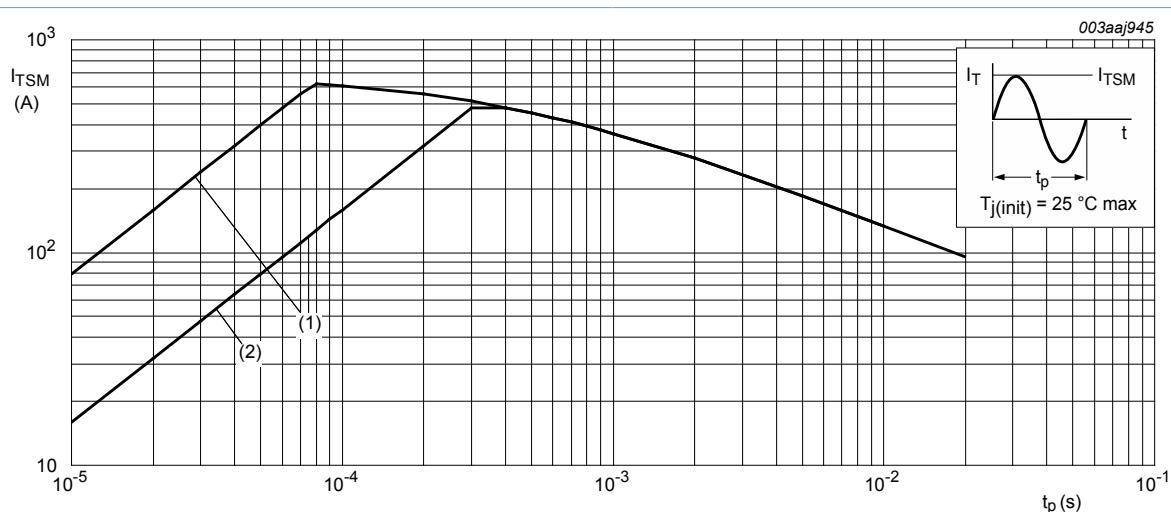


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	1.5	K/W
		half cycle; Fig. 6	-	-	2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint: FR4 board	-	55	-	K/W

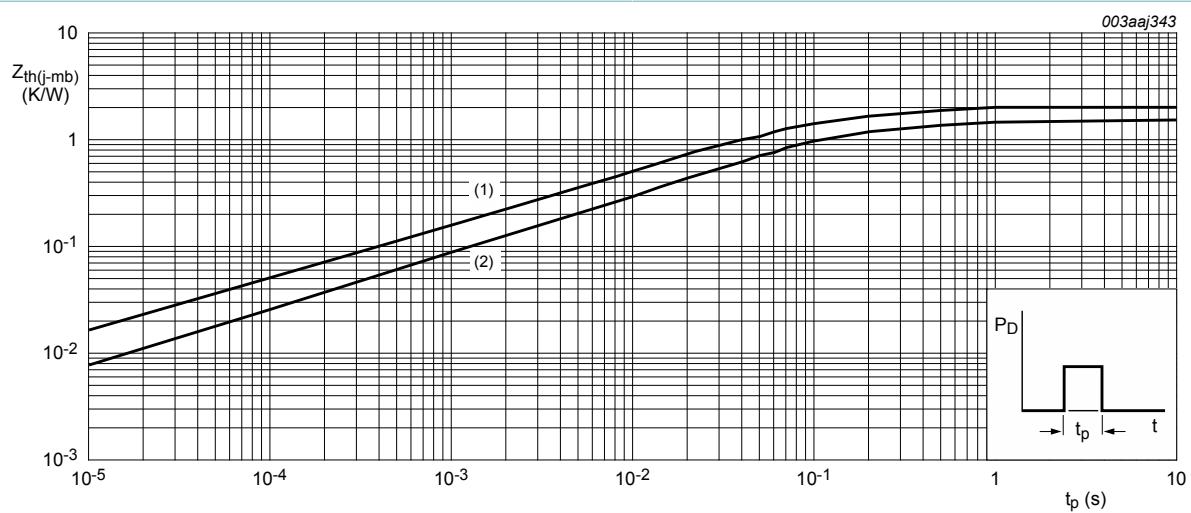
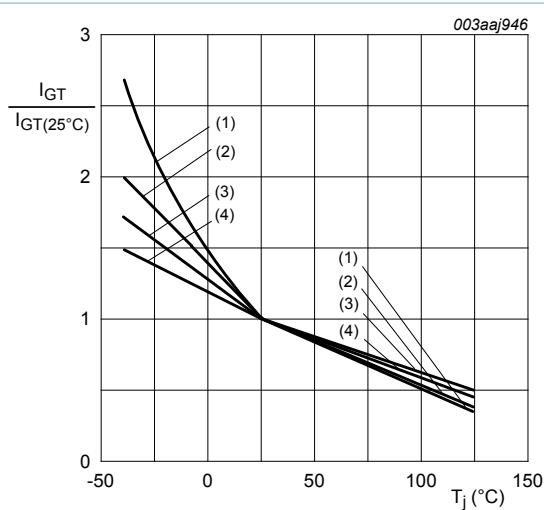


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 7		-	5	50	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 7		-	8	50	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 7		-	10	50	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; Fig. 7		-	22	100	mA
I _L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 8		-	7	60	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 8		-	20	90	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; Fig. 8		-	8	60	mA
		V _D = 12 V; I _G = 0.1 A; T2- G+; T _j = 25 °C; Fig. 8		-	10	90	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 9		-	6	60	mA
V _T	on-state voltage	I _T = 15 A; T _j = 25 °C; Fig. 10		-	1.4	1.65	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11		-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11		0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C		-	0.1	0.5	mA
Dynamic characteristics							
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit		200	250	-	V/μs
t _{gt}	gate-controlled turn-on time	I _{TM} = 16 A; V _D = 600 V; I _G = 0.1 A; dI _G /dt = 5 A/μs		-	2	-	μs



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

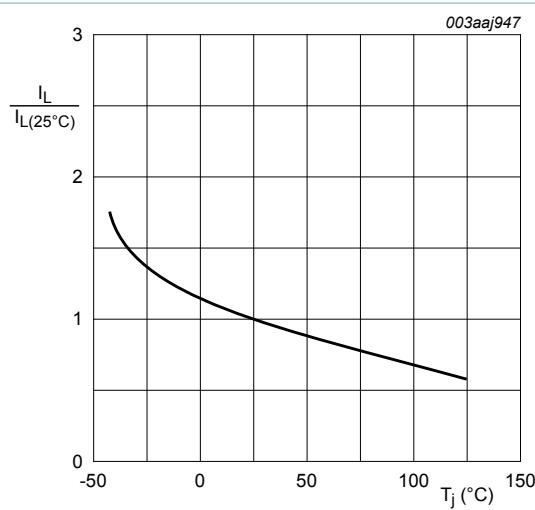


Fig. 8. Normalized latching current as a function of junction temperature

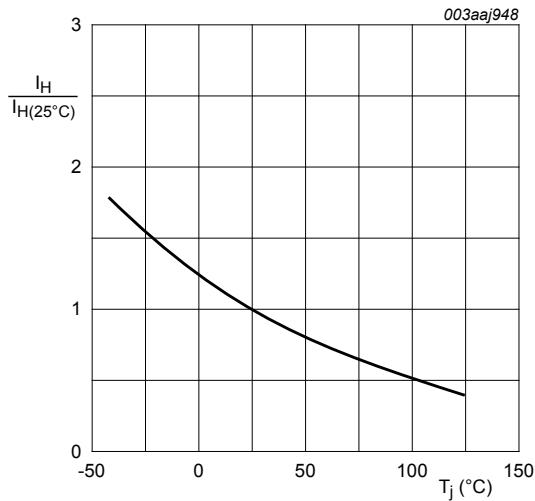
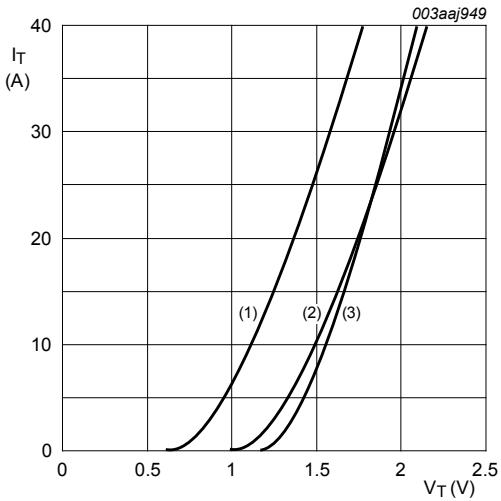


Fig. 9. Normalized holding current as a function of junction temperature



$$V_o = 1.175 \text{ V}; R_s = 0.0316 \Omega$$

- (1) $T_j = 125^\circ\text{C}$; typical values
- (2) $T_j = 125^\circ\text{C}$; maximum values
- (3) $T_j = 25^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

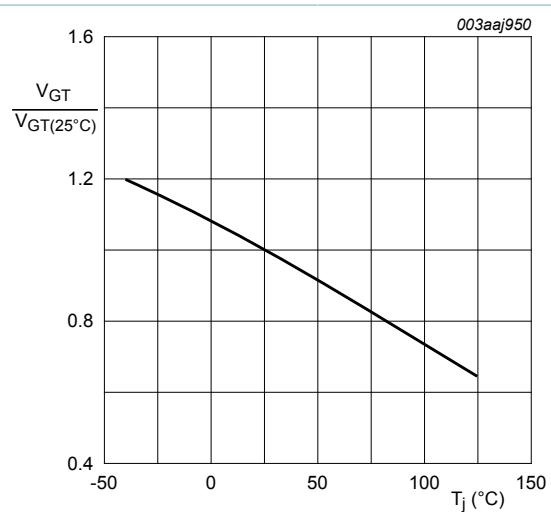


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

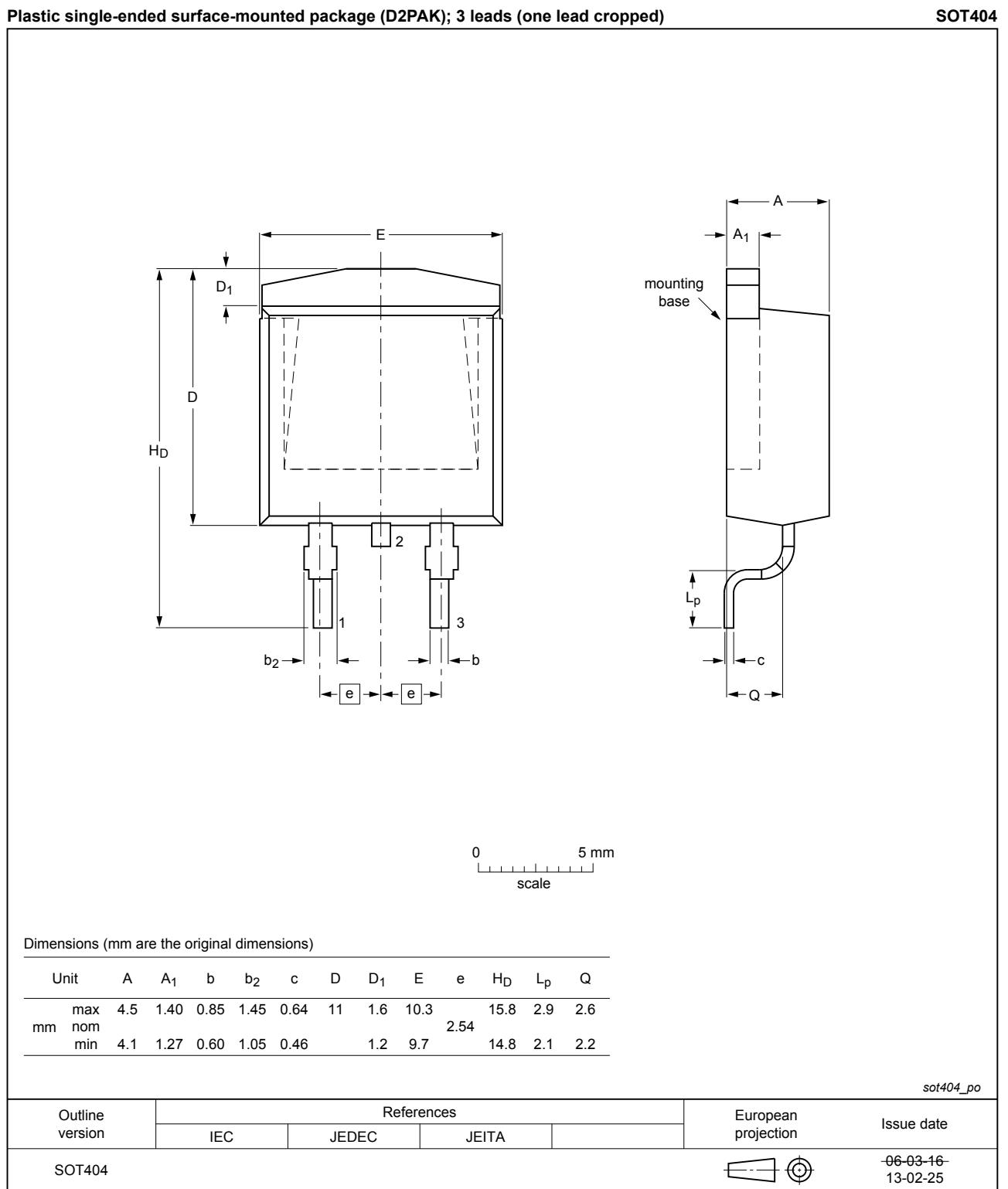


Fig. 12. Package outline D2PAK (SOT404)

11. Soldering

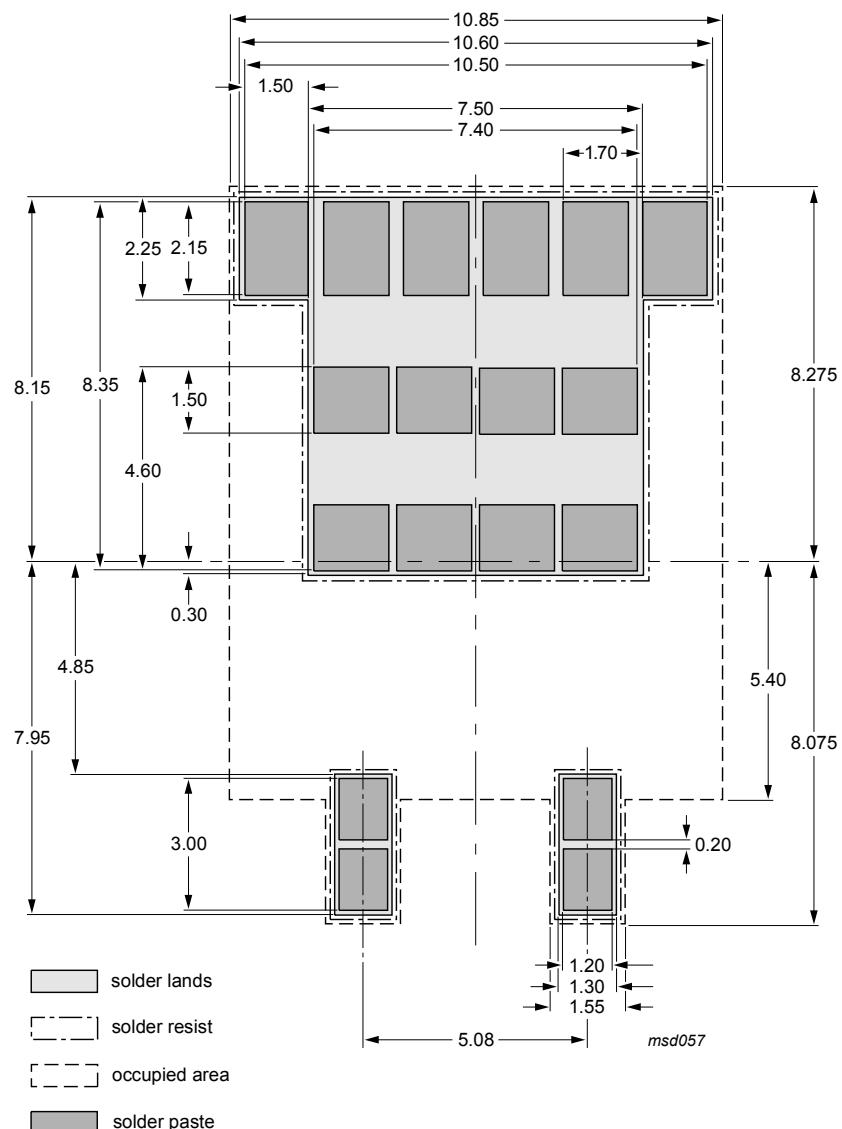


Fig. 13. Reflow soldering footprint for D2PAK (SOT404)

12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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